

HCS90R800S

900V N-Channel Super Junction MOSFET

Features

- Very Low FOM ($R_{DS(on)} \times Q_g$)
- Extremely low switching loss
- Excellent stability and uniformity
- 100% Avalanche Tested
- Built-in ESD Diode

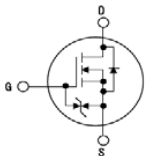
Application

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- TV power & LED Lighting Power
- AC to DC Converters
- Telecom

Key Parameters

Parameter	Value	Unit
$BV_{DSS} @ T_{j,max}$	950	V
I_D	6.7	A
$R_{DS(on), max}$	0.8	Ω
Q_g, Typ	17.4	nC

Package & Internal Circuit

TO-220FS	SYMBOL
	

Absolute Maximum Ratings

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	900	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current - Continuous ($T_C = 25^{\circ}\text{C}$)	6.7 *	A
	Drain Current - Continuous ($T_C = 100^{\circ}\text{C}$)	4.2 *	A
$I_{DM}^{1)}$	Drain Current - Pulsed	20 *	A
$E_{AS}^{2)}$	Single Pulsed Avalanche Energy	83	mJ
I_{AR}	Avalanche Current	1.40	A
dv/dt	MOSFET dv/dt ruggedness, $V_{DS}=0 \dots 400\text{V}$	50	V/ns
dv/dt	Reverse diode dv/dt, $V_{DS}=0 \dots 400\text{V}$, $I_{DS} \leq I_D$	15	V/ns
P_D	Power Dissipation ($T_C = 25^{\circ}\text{C}$)	29	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

* Drain current limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.34	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	80	$^{\circ}\text{C/W}$

Electrical Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
On Characteristics						
V _{GS}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 280 μA	2.0	-	4.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 1.7 A	-	0.696	0.8	Ω
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1mA	900	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 900 V, V _{GS} = 0	-	-	1	μA
		V _{DS} = 900 V, T _C = 150°C	-	-	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±1	μA
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 500 V, V _{GS} = 0 V, f = 1.0 MHz	-	740	-	pF
C _{oss}	Output Capacitance		-	15	-	pF
C _{rss}	Reverse Transfer Capacitance		-	2.8	-	pF
Switching Characteristics						
t _{d(on)}	Turn-On Time	V _{DS} = 450 V, I _D = 3.6 A, R _G = 25 Ω (Note 3,4)	-	23	-	ns
t _r	Turn-On Rise Time		-	20	-	ns
t _{d(off)}	Turn-Off Delay Time		-	91	-	ns
t _f	Turn-Off Fall Time		-	17	-	ns
Q _{g(}	Total Gate Charge	V _{DS} = 720 V, I _D = 3.6 A, V _{GS} = 10 V (Note 3,4)	-	17.4	-	nC
Q _{gs}	Gate-Source Charge		-	3.2	-	nC
Q _{gd}	Gate-Drain Charge		-	5.5	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		-	-	6.7	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-	-	20	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 3.6 A	-	-	1.3	V
trr	Reverse Recovery Time	V _R = 400 V, I _F = 3.6 A di _F /dt = 100 A/μs	-	278	-	ns
Qrr	Reverse Recovery Charge		-	2.3	-	μC

Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS}=1.4\ \text{A}$ $V_{DD}=50\ \text{V}$, $R_G=25\ \Omega$, Starting $T_J=25^\circ\text{C}$
3. Pulse Test : Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$
4. Essentially Independent of Operating Temperature

Typical Characteristics

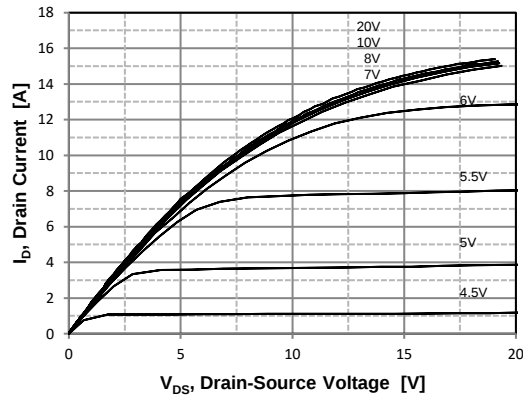


Figure 1. On Region Characteristics

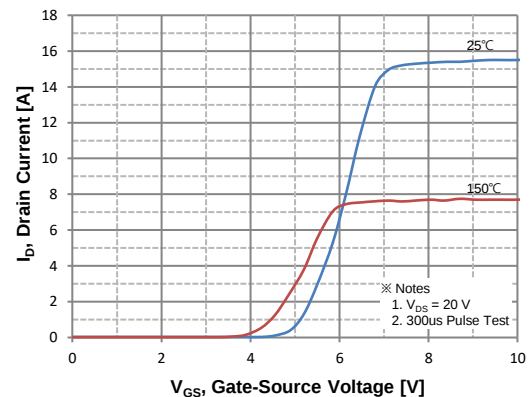


Figure 2. Transfer Characteristics

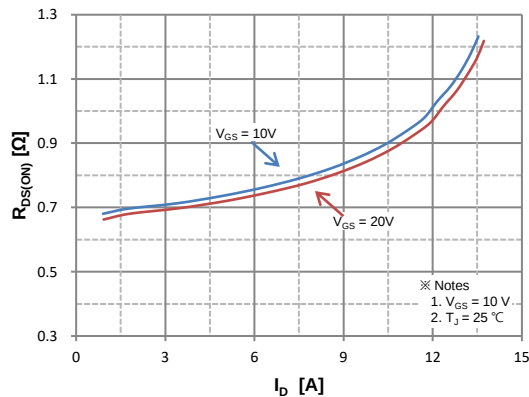


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

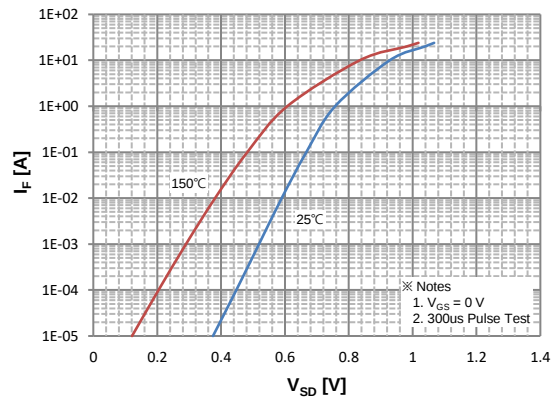


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

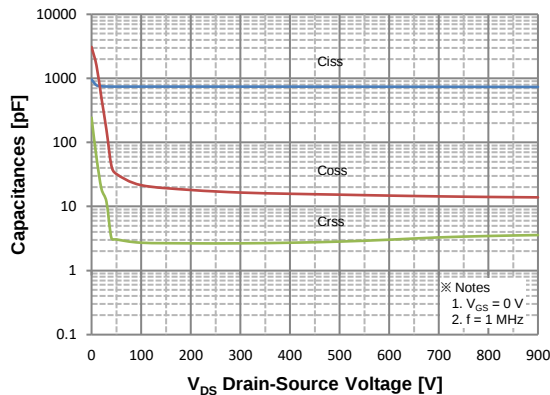


Figure 5. Capacitance Characteristics

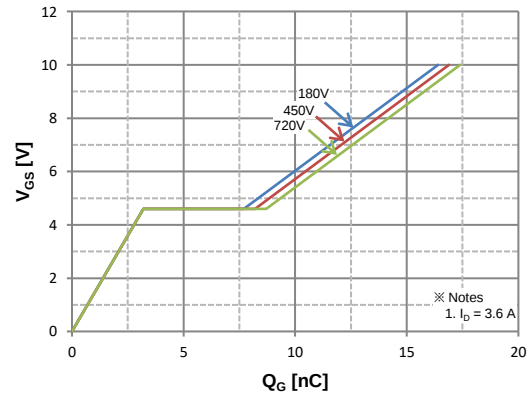


Figure 6. Gate Charge Characteristics

Typical Characteristics

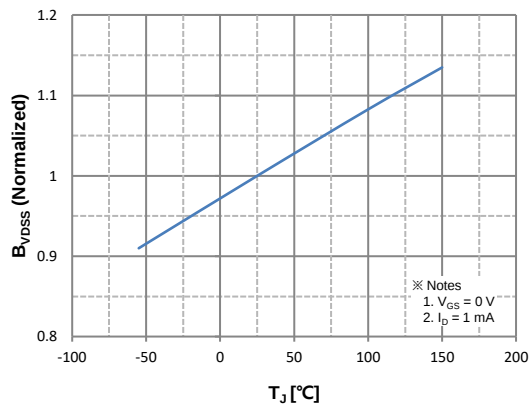


Figure 7. Breakdown Voltage Variation vs. Temperature

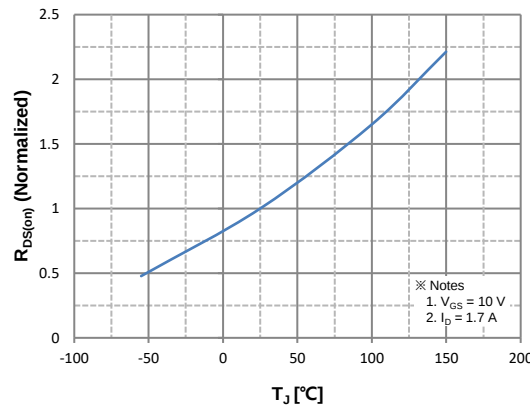


Figure 8. On-Resistance Variation vs. Temperature

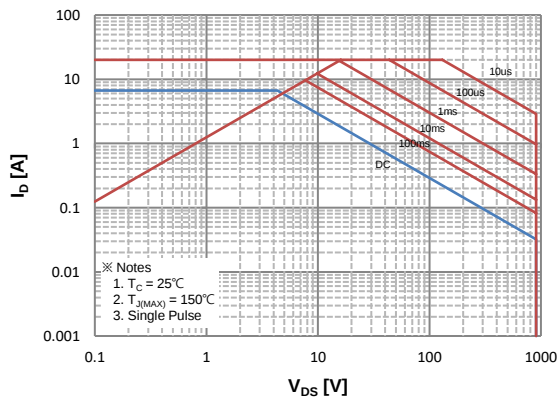


Figure 9. Maximum Safe Operating Area

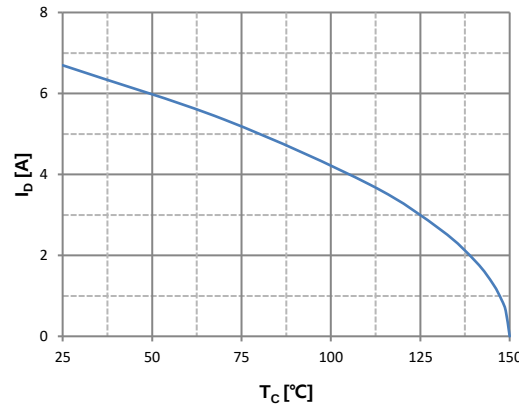


Figure 10. Maximum Drain Current vs. Case Temperature

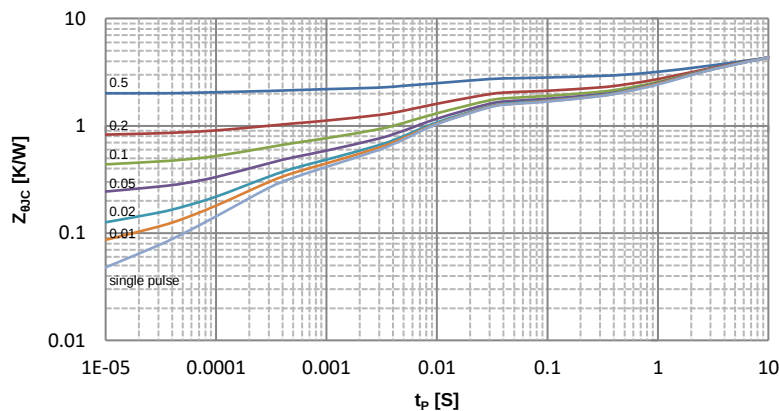


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

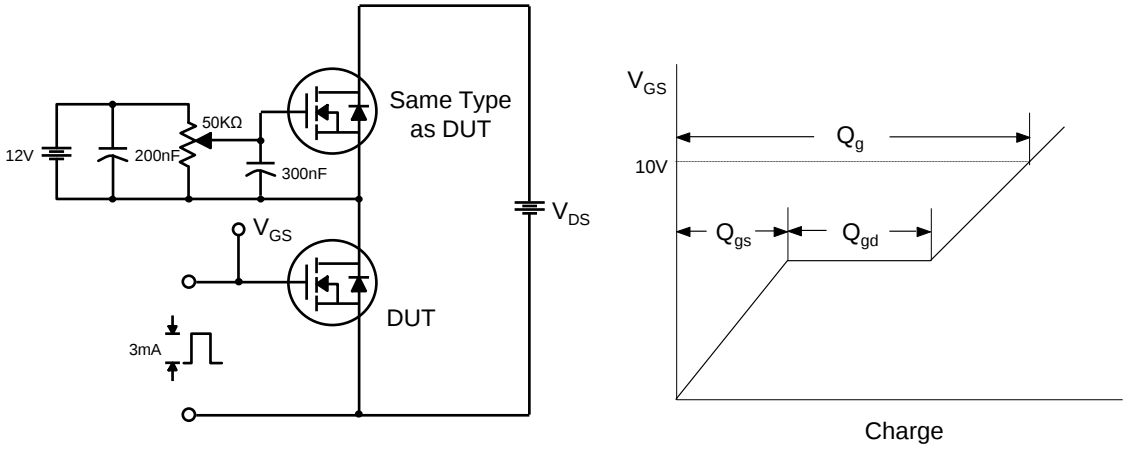


Fig 13. Resistive Switching Test Circuit & Waveforms

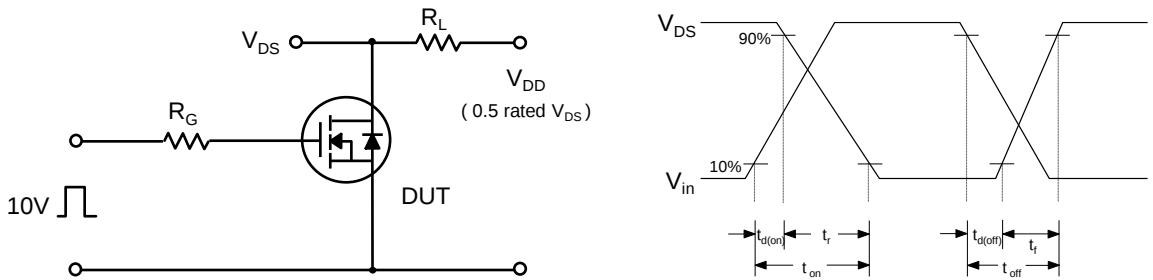
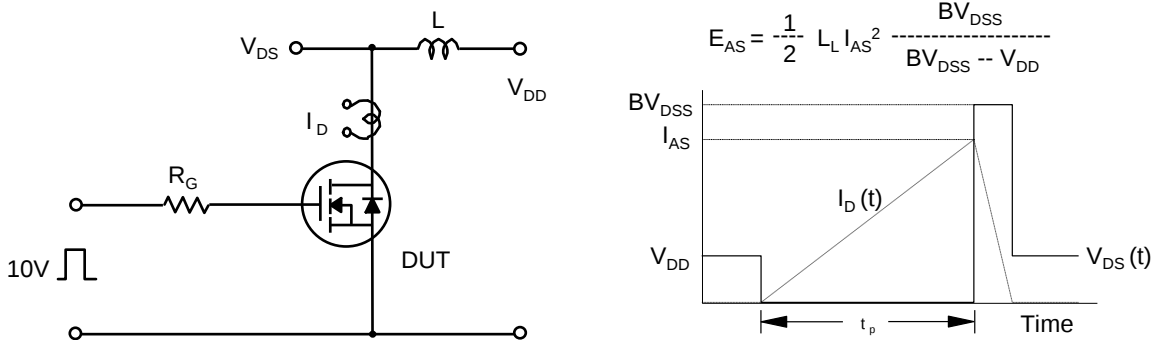


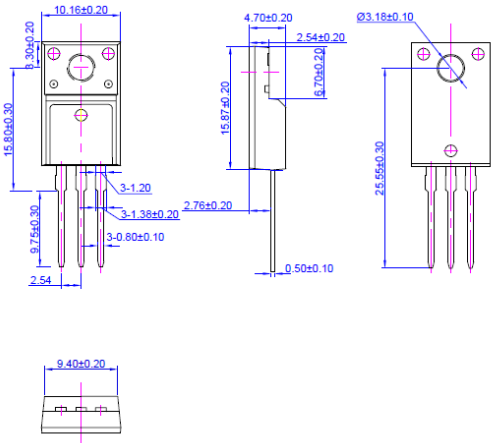
Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

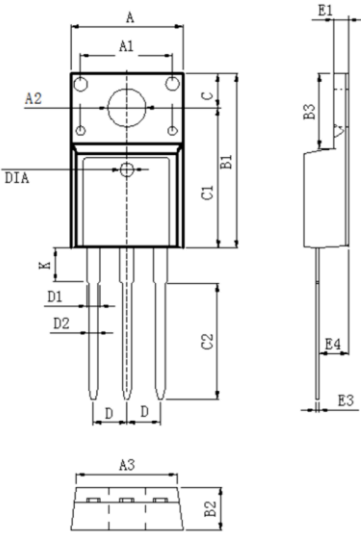
TO-220FS / TO-220FS-FM(Full Mold)

GZSM



- 技术要求:
1. 顶针孔不允许凸出塑封体表面
 2. 标注单位mm
 3. 树脂体不准有缺损、缩孔、裂纹、气泡等有害缺陷
 4. 未标注公差±0.15mm

JINTIAN



DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⌀1.5 (deep 0.2)

Unit:mm

SEMTECH

